

Abstract Submitted  
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**Galvanomagnetic and Thermoelectric Properties of  $\text{Bi}_2\text{Se}_{3-x}\text{S}_x$**   
**Prepared by Spark Plasma Sintering and Annealing**<sup>1</sup> BIN HE, YI-BIN GAO,  
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State University, Columbus, OH; 2 Department of Physics, The Ohio State Univer-  
sity, Columbus OH —  $\text{Bi}_2\text{Se}_3$  belongs to the tetradymite class of semiconductors,  
many of which are known thermoelectric materials.  $\text{Bi}_2\text{Se}_3$  has intrinsic Se vacan-  
cies that tend to make it n-type, and the conduction band density of states (DOS)  
is too low to give a high ZT. Here sulfur is added to pure  $\text{Bi}_2\text{Se}_3$  in order to in-  
crease the DOS and reduce vacancy concentration. A group of  $\text{Bi}_2\text{Se}_{3-x}\text{S}_x$  samples  
are prepared by SPS, with x varying from 0% to 10%. The samples are cut into  
halves, with one half measured directly and the other annealed before measurement.  
Thermoelectric properties are measured from 80K to 420K. The Seebeck coefficient  
increases after annealing while the Hall measurements show the carrier concentration  
to drop from about  $10^{19}/\text{cm}^3$  to about  $10^{18}/\text{cm}^3$ . The DOS increases a little with  
x, as expected, and the best power factor reached is about  $16 \mu\text{W}/\text{cmK}^2$ . While the  
electron concentration can thus be controlled, further work is needed to increase the  
conduction band DOS more.

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